

Innovative Slants for Quality h-GaN Fabrication on Si (111) by MOVPE



GaN as a latest encroachment in compound semiconductor technology, it has lot of potential as a sensor application even in harsh environment, solid state lighting (SSL), blue laser, for space SPV where specific power (W/kg)& power stowed volume (W/m³) are important. GaN thermal conductivity and electron mobility are well compared to Si. It is next important semiconductor material after silicon. So for high power and RF device fabrication, it is very important to assure the device with higher power density/ breakdown voltage and less prone to heat generation. Since GaN is wider direct band gap materials, it is capable to handle higher frequency (at present more than 10 GHz with power densities 10 W/mm) with less junction temperature. In case of Radar & Satellite communication links operating at frequencies ranging from 100 MHz to 90 GHz, have large power requirements. So GaN is well compatible over Si technology for these purposes to minimize power losses as heat. So GaN is a highly prospective compound semiconductor for future green technology. I hope this book as a study based GaN fabrication aspects on Si(111) would be helpful for new learners . Thanks - Dr. Bablu K. Ghosh (UMS)

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